

Title (en)

Light emitting device with an N-face between two n-type semiconductor layers

Title (de)

Lichtemittierende Vorrichtung mit einer N-Kristallfläche an der Grenzfläche zwischen zwei n-leitenden Halbleiterschichten

Title (fr)

Dispositif électroluminescent avec une face N entre deux couches semiconductrices de type-n.

Publication

EP 2405496 A2 20120111 (EN)

Application

EP 11173189 A 20110708

Priority

KR 20100065976 A 20100708

Abstract (en)

Disclosed is a light emitting device (100) including a substrate (140), a reflective layer (130) provided on the substrate, and a light emitting structure (101), which includes a first conductive semiconductor layer (120), a second conductive semiconductor layer (170) and an active layer (160) placed between the first and second conductive semiconductor layers, wherein the first conductive semiconductor layer is n-type, including GaN and doped with an n-type dopant, wherein the first conductive semiconductor layer includes a first n-type semiconductor layer (121) and a second n-type semiconductor layer (122) between the first n-type semiconductor layer and the active layer, wherein the contact surface between the first and second n-type semiconductor layers is an N-face. The disclosed light emitting device may have improved luminous efficacy while showing reduction in crystal defects.

IPC 8 full level

H01L 33/02 (2010.01); **H01L 33/00** (2010.01); **H01L 33/10** (2010.01); **H01L 33/32** (2010.01)

CPC (source: EP US)

H01L 33/02 (2013.01 - EP US); **H01L 33/10** (2013.01 - EP US); **H01L 33/32** (2013.01 - EP US); **H01L 2224/48091** (2013.01 - EP US); **H01L 2224/48247** (2013.01 - EP US)

Citation (applicant)

KR 20100065976 A 20100617 - LEE TAE SU [KR]

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

EP 2405496 A2 20120111; **EP 2405496 A3 20141105**; CN 102315349 A 20120111; CN 102315349 B 20160427; KR 101659738 B1 20160926; KR 20120005298 A 20120116; US 2012007100 A1 20120112; US 8405093 B2 20130326

DOCDB simple family (application)

EP 11173189 A 20110708; CN 201110197898 A 20110708; KR 20100065976 A 20100708; US 201113178171 A 20110707